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## **ACCEPTED MANUSCRIPT**

## Characterisation of Cs ion implanted GaN by DLTS

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#### **Abstract**

Deep level transient spectroscopy (DLTS) was used to characterise Cs implanted GaN grown by hydride vapour phase epitaxy (HVPE). This implantation was done at room temperature using energy of 360 keV to a fluence of  $10^{-11}$  cm<sup>-2</sup>. A defect with activation energy of 0.19 eV below the conduction band and an apparent capture cross section of  $1.1 \times 10^{-15}$  cm<sup>2</sup> was induced. This defect has previously been observed after rare earth element (Eu, Er and Pr) implantation. It has also been reported after electron, proton and He ion implantation.

Keywords: GaN; Cs implantation; Defect; DLTS

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